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Zn/sup +//P/sup +/ and Zn/sup +//As/sup +/ co-implantation in InP single crystals

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Abstract

The activation efficiency of zinc impurity co-implanted with P/sup +/ and As/sup +/ ions in InP was studied by Hall-effect measurements. Both P/sup +/ and As/sup +/ co-implantations followed by post-implantation annealing at 400 to 600/spl deg/C in InP single crystals have been found to result in a decrease of impurity activation. At the same time an improvement of activation efficiency was observed at annealing temperatures T/sub ann/>600/spl deg/C.

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